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Assistant Commissioner for Patents  
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On July 2, 2002

TOWNSEND and TOWNSEND and CREW LLP

By: Lisa Karen

Attorney Docket No.: 082666-000100US  
Client Ref. No.: 0338-4033USD

PATENT

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TECHNOLOGY CENTER 2800

#15/B  
And  
8/2/02

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re application of:

Jin-Kuo Ho, et al.

Application No.: 09/388,265

Filed: September 1, 1999

For: OHMIC CONTACT TO  
SEMICONDUCTOR DEVICES AND  
METHOD OF MANUFACTURING THE  
SAME

Examiner: H. Vu

Art Unit: 2811

PRELIMINARY AMENDMENT

Assistant Commissioner for Patents  
Washington, D.C. 20231

Sir:

Prior to examination of the above-referenced application, please enter the following amendments and remarks.

IN THE CLAIMS:

Please amend claim 8 as follows:

8. (Twice Amended) An ohmic contact in a semiconductor device which is formed on a p-type semiconductor material, the ohmic contact comprising a layer of p-type semiconductor oxide and metal in a condition of mixed morphology.

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